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## NTE74HCT374 Integrated Circuit TTL – High Speed CMOS, Octal D–Type Flip–Flop with 3–State Outputs, Common Output Control & Common Clock

**Description:**

The NTE74HCT374 is an octal D–type flip–flop in a 20–Lead DIP type package that uses advanced silicon–gate CMOS technology, which provides the inherent benefits of low power consumption and wide power supply range, but are LS–TTL input and output characteristic and pin–out compatible. The 3–STATE outputs are capable of driving 15 LS–TTL loads. All inputs are protected from damage due to static discharge by internal diodes to  $V_{CC}$  and GND.

The NTE74HCT374 is a positive edge triggered flip–flop. Data at the D inputs, meeting the setup and hold time requirements, are transferred to the Q outputs on positive going transitions of the CLOCK (CK) input. When a high logic level is applied to the OUTPUT CONTROL (OC) input, all outputs go to a high impedance state, regardless of what signals are present at the other inputs and the state of the storage elements.

NTE74HCT devices are intended to interface between TTL and NMOS components and standard CMOS devices. These devices are also plug–in replacements to LS–TTL devices and can be used to reduce power consumption in existing designs.

**Features:**

- TTL Input Characteristic Compatible
- Typical Propagation Delay: 20ns
- Low Input Current: 1 $\mu$ A (max)
- Low Quiescent Current: 80 $\mu$ A (max)
- Compatible with Bus–Oriented Systems
- High Output Drive Capability: 15 LS–TTL Loads

**Absolute Maximum Ratings:** (Note 1, Note 2)

Supply Voltage, $V_{CC}$ .....	-0.5 to +7.0V
DC Input Voltage, $V_{IN}$ .....	-1.5 to $V_{CC}$ +1.5V
DC Output Voltage, $V_{OUT}$ .....	-0.5 to $V_{CC}$ + 0.5V
Clamp Diode Current, $I_{IK}, I_{OK}$ .....	$\pm$ 20mA
DC Output Current (Per Pin), $I_{OUT}$ .....	$\pm$ 35mA
DC $V_{CC}$ or GND Current (Per Pin), $I_{CC}$ .....	$\pm$ 70mA
Power Dissipation (Note 3), $P_D$ .....	600mW
Storage Temperature Range, $T_{stg}$ .....	-65° to +150°C
Lead Temperature (During Soldering, 10sec), $T_L$ .....	+260°C

Note 1. Absolute Maximum Ratings are those values beyond which damage to the device may occur.  
 Note 2. Unless otherwise specified, all voltages are referenced to GND.  
 Note 3. Power Dissipation temperature derating: 12mW/°C from +65°C to +85°C.

### Recommended Operating Conditions:

Parameter	Symbol	Min	Typ	Max	Unit
Supply Voltage	$V_{CC}$	4.5	–	5.5	V
DC Input or Output Voltage	$V_{IN}, V_{OUT}$	0	–	$V_{CC}$	V
Operating Temperature Range	$T_A$	–40	–	+85	°C
Input Rise or Fall Times	$t_r, t_f$	–	–	500	ns

### DC Electrical Characteristics: ( $V_{CC} = 5V \pm 10\%$ unless otherwise specified)

Parameter	Symbol	Test Conditions	$T_A = +25^\circ\text{C}$		$T_A = -40^\circ\text{ to } +85^\circ\text{C}$		Unit
			Typ	Guaranteed Limits			
Minimum High Level Input Voltage	$V_{IH}$		–	2.0	2.0		V
Maximum Low Level Input Voltage	$V_{IL}$		–	0.8	0.8		V
Minimum High Level Output Voltage	$V_{OH}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$ I_{OUT}  = 20\mu\text{A}$	$V_{CC}$	$V_{CC}^{-0.1}$		V
			$ I_{OUT}  = 6.0\text{mA}, V_{CC} = 4.5\text{V}$	4.2	3.98	3.84	V
			$ I_{OUT}  = 7.2\text{mA}, V_{CC} = 5.5\text{V}$	5.7	4.98	4.84	V
Maximum Low Level Output Voltage	$V_{OL}$	$V_{IN} = V_{IH}$	$ I_{OUT}  = 20\mu\text{A}$	0	0.1		V
			$ I_{OUT}  = 6.0\text{mA}, V_{CC} = 4.5\text{V}$	0.2	0.26	0.33	V
			$ I_{OUT}  = 7.2\text{mA}, V_{CC} = 5.5\text{V}$	0.2	0.26	0.33	V
Maximum Input Current	$I_{IN}$	$V_{IN} = V_{CC}$ or GND, $V_{IH}$ or $V_{IL}$	–	$\pm 0.1$	$\pm 1.0$		$\mu\text{A}$
Maximum 3–STATE Output Leakage Current	$I_{OZ}$	$V_{OUT} = V_{CC}$ or GND, $\bar{G} = V_{IH}$ , $G = V_{IL}$	–	$\pm 0.5$	$\pm 5.0$		$\mu\text{A}$
Maximum Quiescent Supply Current	$I_{CC}$	$V_{IN} = V_{CC}$ or GND, $I_{OUT} = 0\mu\text{A}$	–	8.0	80		$\mu\text{A}$
		$V_{IN} = 2.4\text{V}$ or 0.5V, Note 4	–	1.0	1.3		mA

Note 4. This is measured per input with all other inputs held at  $V_{CC}$  or GND.

### AC Electrical Characteristics: ( $V_{CC} = 5V$ , $t_r = t_f = 6\text{ns}$ , $T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Typ	Guaranteed Limits	Unit
Maximum Clock Frequency	$f_{MAX}$		50	30	MHz
Maximum Propagation Delay to Output	$t_{PHL}, t_{PLH}$	$C_L = 45\text{pF}$	20	32	ns
Maximum Enable Propagation Delay, Control to Output	$t_{PZH}, t_{PZL}$	$C_L = 45\text{pF}, R_L = 1\text{k}\Omega$	19	28	ns
Maximum Disable Propagation Delay, Control to Output	$t_{PLZ}, t_{PHZ}$	$C_L = 5\text{pF}, R_L = 1\text{k}\Omega$	17	25	ns
Minimum Clock Pulse Width	$t_W$		–	20	ns
Minimum Setup Time Data to Clock	$t_S$		–	5	ns
Minimum Hold Time Clock to Data	$t_H$		–	16	ns

### AC Electrical Characteristics: ( $V_{CC} = 5V \pm 10\%$ , $t_r = t_f = 6\text{ns}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	$T_A = +25^\circ\text{C}$		$T_A = -40^\circ\text{ to } +85^\circ\text{C}$		Unit
			Typ	Guaranteed Limits			
Maximum Clock Frequency	$f_{MAX}$		–	30	24		MHz
Maximum Propagation Delay to Output	$t_{PHL}, t_{PLH}$	$C_L = 50\text{pF}$	22	36	45		ns
		$C_L = 150\text{pF}$	30	46	57		ns
Maximum Enable Propagation Delay Control to Output	$t_{PHL}, t_{PLH}$	$C_L = 50\text{pF}$	21	30	37		ns
		$C_L = 150\text{pF}$	30	40	50		ns

**AC Electrical Characteristics (Cont'd):** ( $V_{CC} = 5V \pm 10\%$ ,  $t_r = t_f = 6ns$  unless otherwise specified)

Parameter	Symbol	Test Conditions	$T_A = +25^\circ C$		$T_A = -40^\circ \text{ to } +85^\circ C$		Unit
			Typ	Guaranteed Limits			
Maximum Disable Propagation Delay Control to Output	$t_{PHZ}, t_{PLZ}$	$R_L = 1k\Omega, C_L = 50pF$	21	30	37		ns
Maximum Output Rise and Fall Time	$t_{THL}, t_{TLH}$	$C_L = 50pF$	8	12	15		ns
Minimum Clock Pulse Width	$t_W$		-	16	20		ns
Minimum Setup Time Data to Clock	$t_S$		-	20	25		ns
Minimum Hold Time Clock to Data	$t_H$		-	5	5		ns
Maximum Input Capacitance	$C_{IN}$		-	10	10		pF
Maximum Output Capacitance	$C_{OUT}$		-	20	20		pF
Power Dissipation Capacitance (Note 5)	$C_{PD}$	$OC = V_{CC}$	5	-	-		pF
		$OC = GND$	58	-	-		pF

Note 5.  $C_{PD}$  determines the no load dynamic power consumption,  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ , and the no load dynamic current consumption,  $I_S = C_{PD} V_{CC} f + I_{CC}$ .

**Truth Table:**

Output Control	LE	Data	Output
L	↑	H	H
L	↑	L	L
L	L	X	$Q_0$
H	X	X	Z

H = HIGH Level

L = LOW Level

X = Don't Care

↑ = Transition from LOW-to-HIGH

$Q_0$  = Level of output before steady-state input conditions were established.

Z = High Impedance

### Pin Connection Diagram

